Product data sheet

1. General description

PNP low V_{CEsat} transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements.
- AEC-Q101 qualified

3. Applications

- Power management
 - DC/DC converters
 - · Supply line switching
 - Battery charger
 - · LCD backlighting.
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - · Inductive load driver (e.g. relays, buzzers and motors).

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-30	V
I _C	collector current		[1]	-	-	-3	Α
I _{CM}	peak collector current	limited by T _{j(max)}		-	-	-5	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	80	107	mΩ

[1] Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		, , , , , , , , , , , , , , , , , , ,
3	В	base	3 2 1	B—[
			SOT89	sym132

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS5330X		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5330X	%1S

[1] % = placeholder for manufacturing site code

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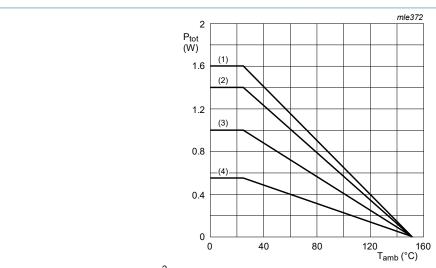
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-30	V
V_{CEO}	collector-emitter voltage	open base		-	-30	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current		[1]	-	-3	А
I _{CM}	peak collector current	limited by T _{j(max)}		-	-5	А
I _B	base current			-	-0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	550	mW
			[3]	-	1	W
			[4]	-	1.4	W
			[1]	-	1.6	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm² [3]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) Ceramic PCB; 7 cm² mounting pad for collector (2) FR4 PCB; 6 cm² copper mounting pad for collector (3) FR4 PCB; 1 cm² copper mounting pad for collector
- (4) Standard footprint

Power derating curves Fig. 1.

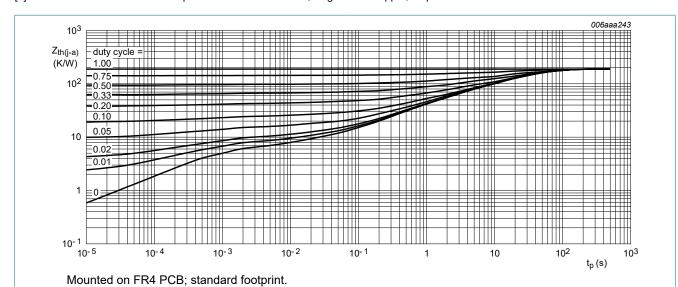
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9. Thermal characteristics

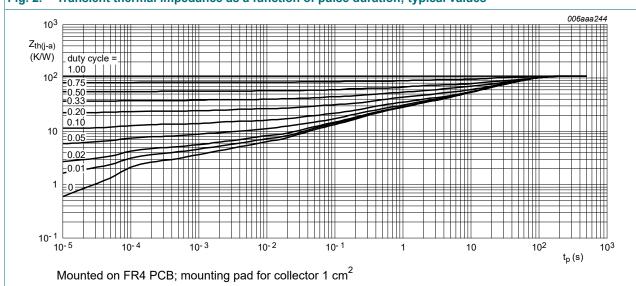
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)	thermal resistance from	in free air	[1]	-	-	225	K/W
	junction to ambient	[2]	-	-	125	K/W	
		[3]	-	-	90	K/W	
			[4]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated. [3]
- [4]

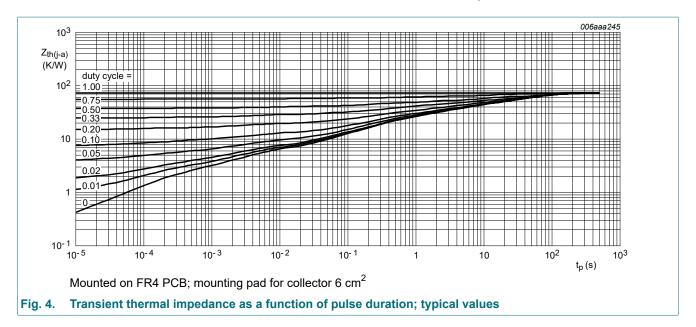


Transient thermal impedance as a function of pulse duration; typical values Fig. 2.



Transient thermal impedance as a function of pulse duration; typical values

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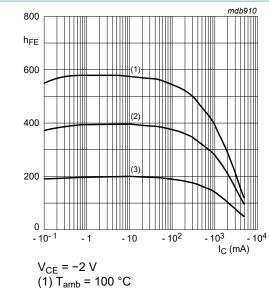
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
ЕВО	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; I _C = -0.1 A; T _{amb} = 25 °C	200	-	-	
		V _{CE} = -2 V; I _C = -0.5 A; T _{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	175	-	450	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	140	-	-	
		V_{CE} = -2 V; I_{C} = -3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	-	-	
V _{CEsat}	collector-emitter	$I_C = -0.5 \text{ A}; I_B = -50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-70	mV
	saturation voltage	I _C = -1 A; I _B = -50 mA; T _{amb} = 25 °C	-	-	-130	mV
		$I_C = -2 \text{ A}; I_B = -100 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-240	mV
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$	-	-	-320	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	80	107	mΩ
V _{BEsat}	base-emitter saturation	I _C = -2 A; I _B = -100 mA; T _{amb} = 25 °C	-	-	-1.1	V
	voltage	I_C = -3 A; I_B = -300 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -1 \text{ A}; T_{amb} = 25 \text{ °C}$	-1	-	-	V
fт	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	45	pF

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$$V_{CE} = -2 V$$

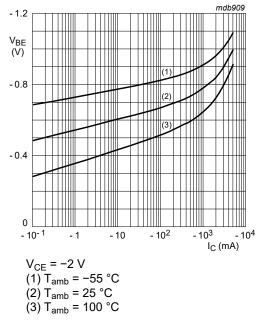
$$(1) T_{amb} = 100 ° ($$

(1)
$$T_{amb} = 100^{\circ} \text{C}$$

(2) $T_{amb} = 25^{\circ} \text{C}$
(3) $T_{amb} = -55^{\circ} \text{C}$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 5. DC current gain as a function of collector current; typical values

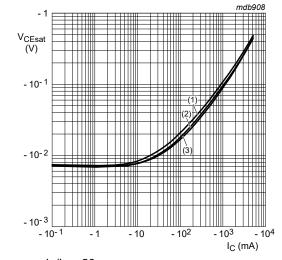


$$(1) T_{amb} = -55 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Base-emitter voltage as a function of collector Fig. 6. current; typical values



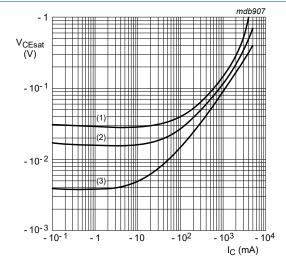
$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

$$(1) I_{\rm C}/I_{\rm B} = 100$$

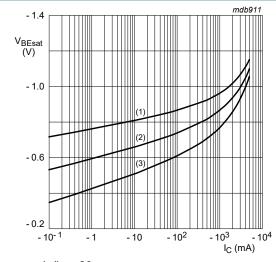
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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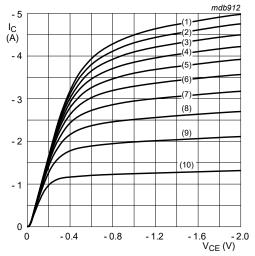
 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = -55$ °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values



 T_{amb} = 25 °C

(1) $I_B = 53.0 \text{ mA}$

 $(2) I_B = 47.7 \text{ mA}$

 $(3) I_B = 42.4 \text{ mA}$

 $(4) I_B = 37.1 \text{ mA}$

 $(5) I_B = 31.8 \text{ mA}$ (6) $I_B = 26.5 \text{ mA}$

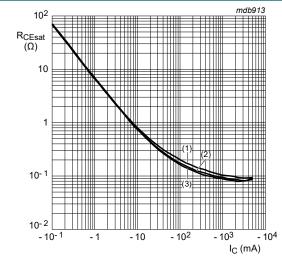
 $(7) I_B = 21.2 \text{ mA}$

(8) $I_B = 15.9 \text{ mA}$

 $(9) I_B = 10.6 \text{ mA}$

 $(10) I_B = 5.3 \text{ mA}$

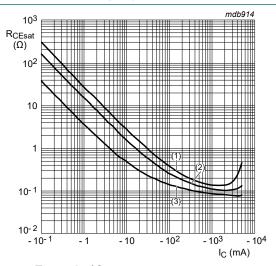
Fig. 10. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 20$

 $(1) T_{amb} = 100 °C$ $(2) T_{amb} = 25 °C$ $(3) T_{amb} = -55 °C$

Fig. 11. Equivalent on-resistance as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C.$ (1) $I_{C}/I_{B} = 10$

(2) $I_C/I_B = 5$

(3) $I_C/I_B = 1$

Fig. 12. Equivalent on-resistance as a function of collector current; typical values

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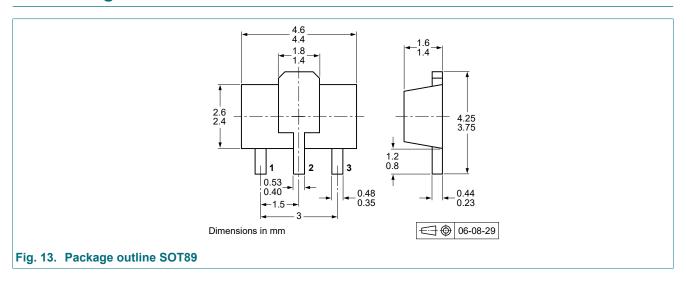
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11. Test information

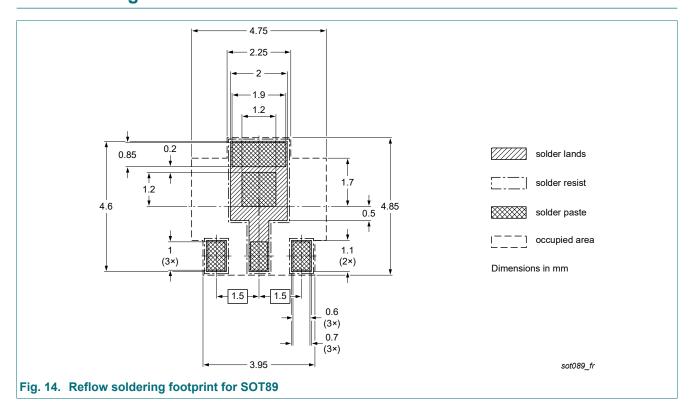
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 -Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

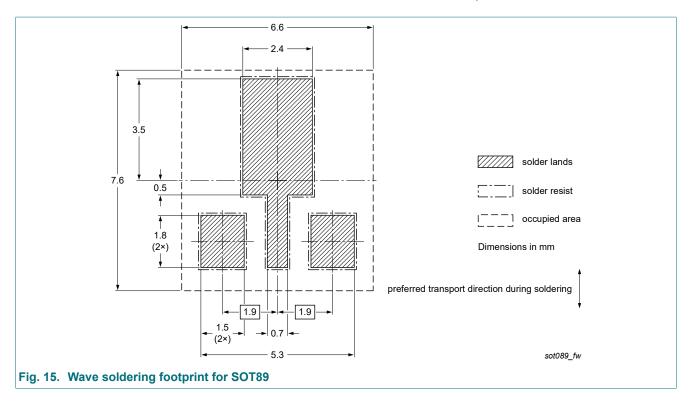
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Tubic of Itorioloff II						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5330X v.3	20250813	Product data sheet	-	PBSS5330X v.2		
Modifications	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 					
PBSS5330X v.2	20041103	Product data sheet	-	PBSS5330X v.1		
PBSS5330X v.1	20031128	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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